

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
20V	0.45Ω @ V _{GS} = 4.5V	1.3A
	0.6Ω @ V _{GS} = 2.5V	1.2A

Features and Benefits

- Footprint of Just 0.6mm²—13 Times Smaller Than SOT23
- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

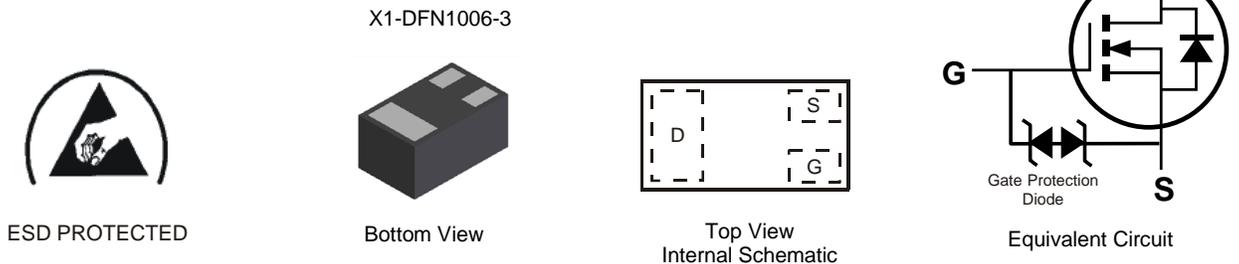
Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Portable Electronics

Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu Over Copper Leadframe. Solderable per MIL-STD-202, Method 208 [e4](#)
- Weight: 0.001 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2710UFB-7	X1-DFN1006-3	3,000/Tape & Reel
DMN2710UFB-7B	X1-DFN1006-3	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±6	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	1.3	A
		T _A = +70°C		1.1	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	5	A
Maximum Body Diode Forward Current (Note 6)			I _S	1.3	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.72	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	174	°C/W
Total Power Dissipation (Note 6)			P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	96	°C/W
Thermal Resistance, Junction to Case (Note 6)			R _{θJC}	117	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	100	nA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.13	0.45	Ω	V _{GS} = 4.5V, I _D = 600mA
		—	0.17	0.6		V _{GS} = 2.5V, I _D = 500mA
		—	0.25	0.75		V _{GS} = 1.8V, I _D = 350mA
		—	—	—		V _{GS} = 1.8V, I _D = 350mA
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 150mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	42	—	pF	V _{DS} = 16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	13	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	6.5	—	pF	
Total Gate Charge	Q _g	—	0.6	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	14	—	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 47Ω, R _g = 10Ω I _D = 200mA
Turn-On Rise Time	t _r	—	19	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	57	—	ns	
Turn-Off Fall Time	t _f	—	65	—	ns	
Reverse Recovery Time	t _{RR}	—	88	—	ns	I _F = 1A, di/dt = 100A/μs
Reverse Recovery Charge	Q _R	—	29	—	nC	I _F = 1A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

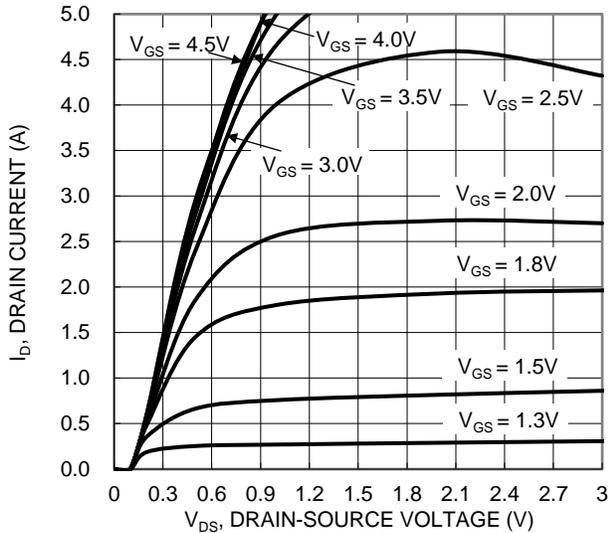


Figure 1. Typical Output Characteristic

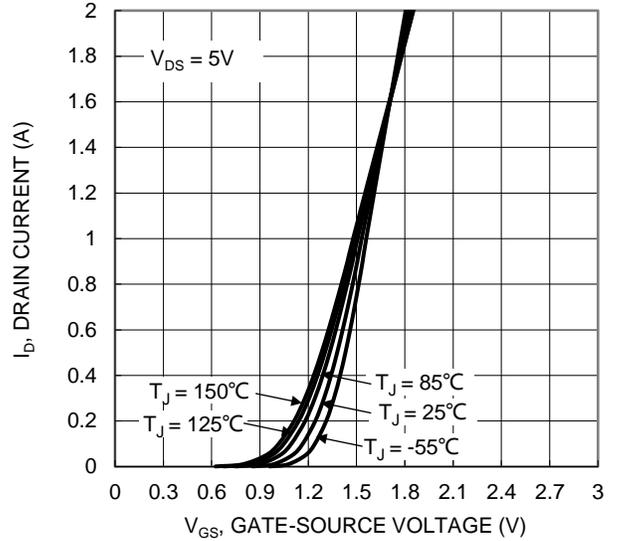


Figure 2. Typical Transfer Characteristic

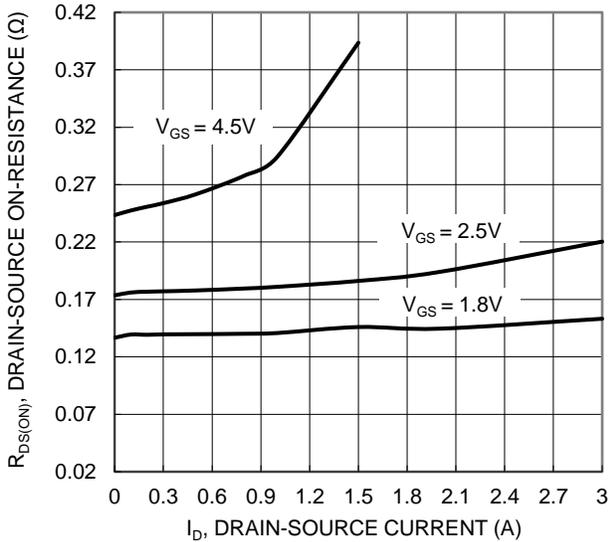


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

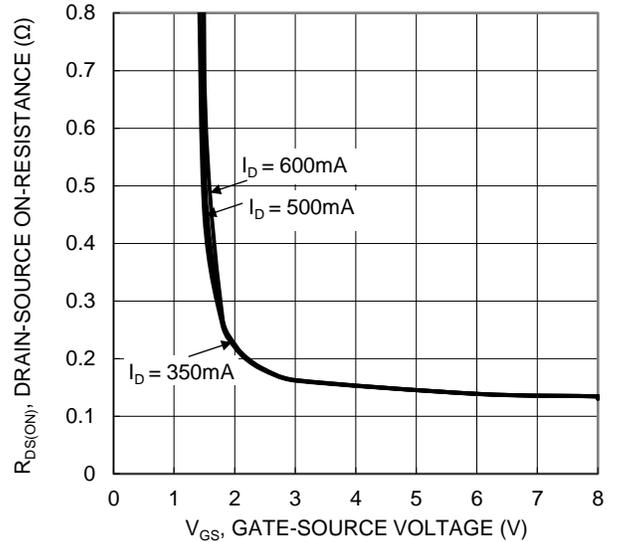


Figure 4. Typical Transfer Characteristic

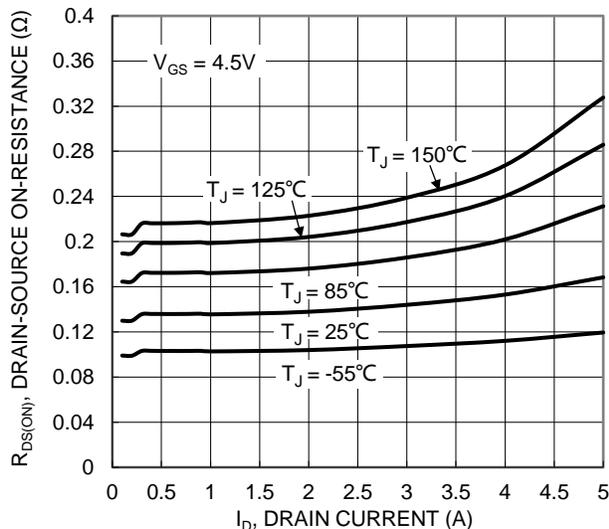


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

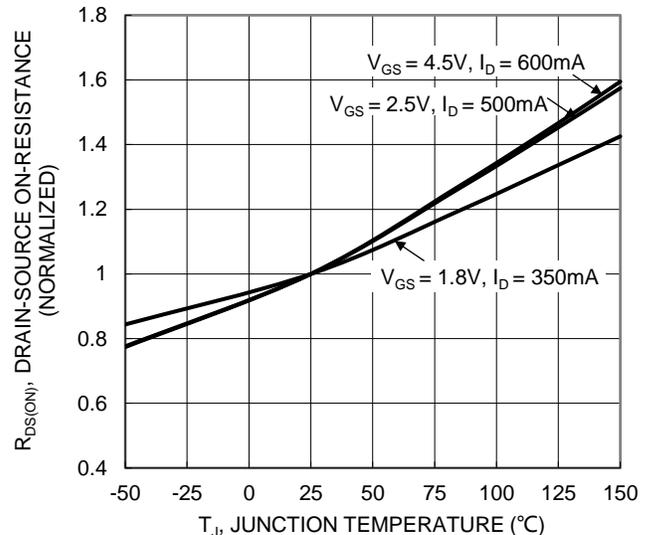


Figure 6. On-Resistance Variation with Temperature

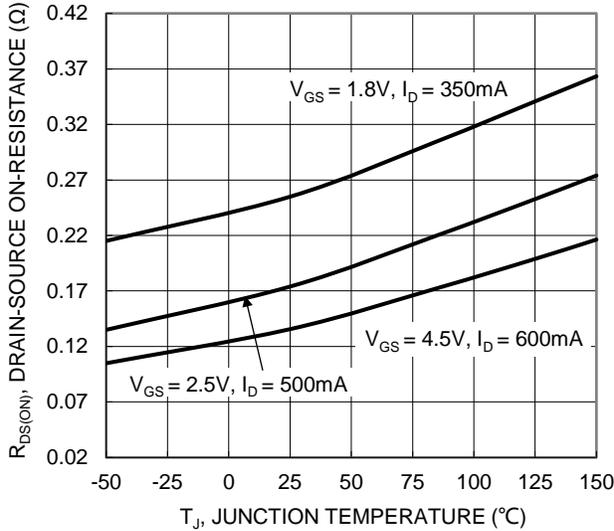


Figure 7. On-Resistance Variation with Temperature

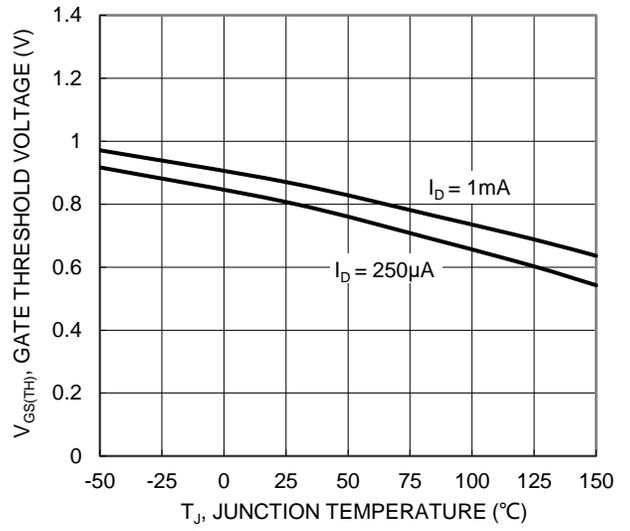


Figure 8. Gate Threshold Variation vs. Junction Temperature

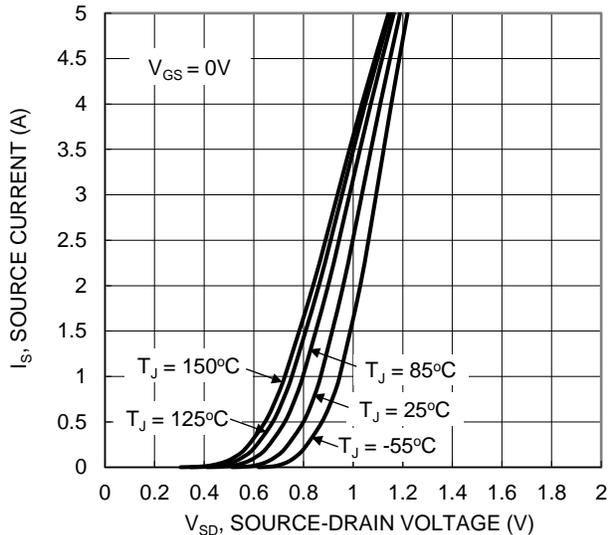


Figure 9. Diode Forward Voltage vs. Current

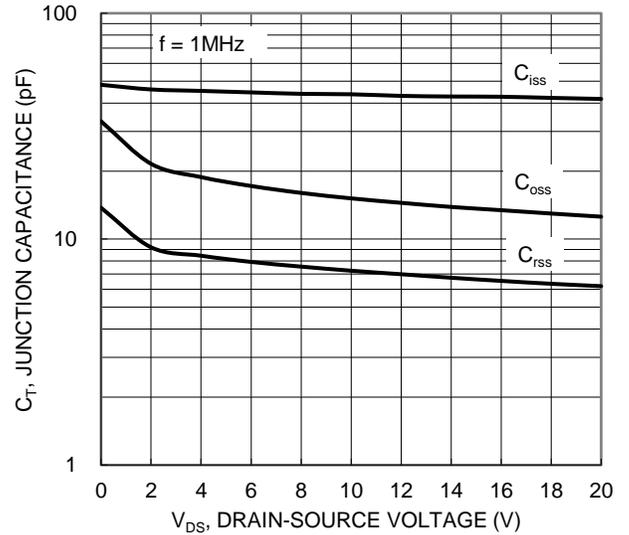


Figure 10. Typical Junction Capacitance

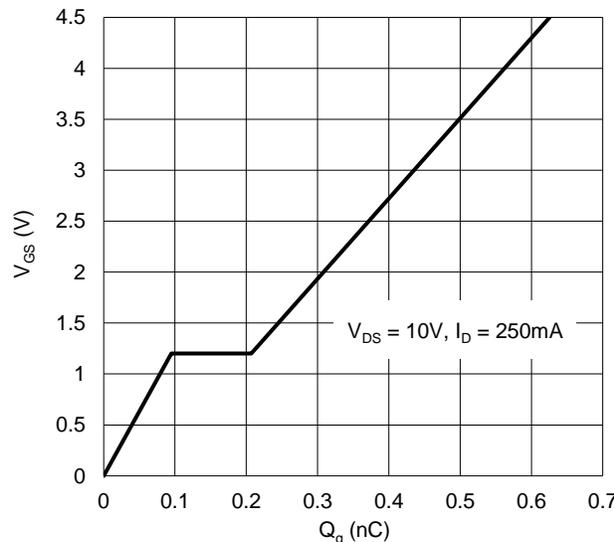


Figure 11. Gate Charge

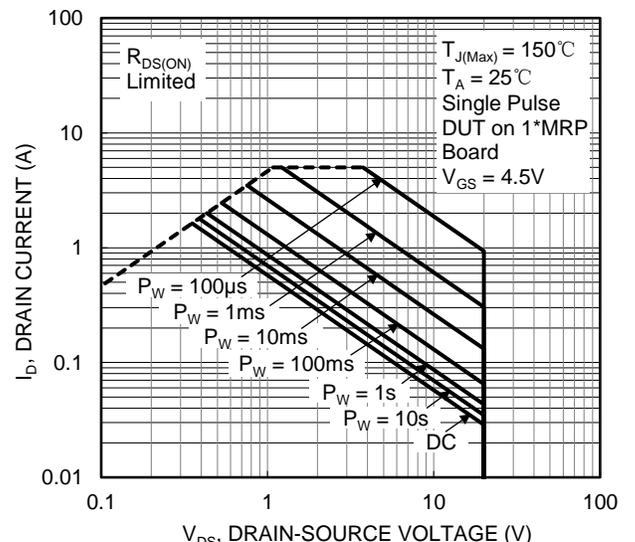


Figure 12. SOA, Safe Operation Area

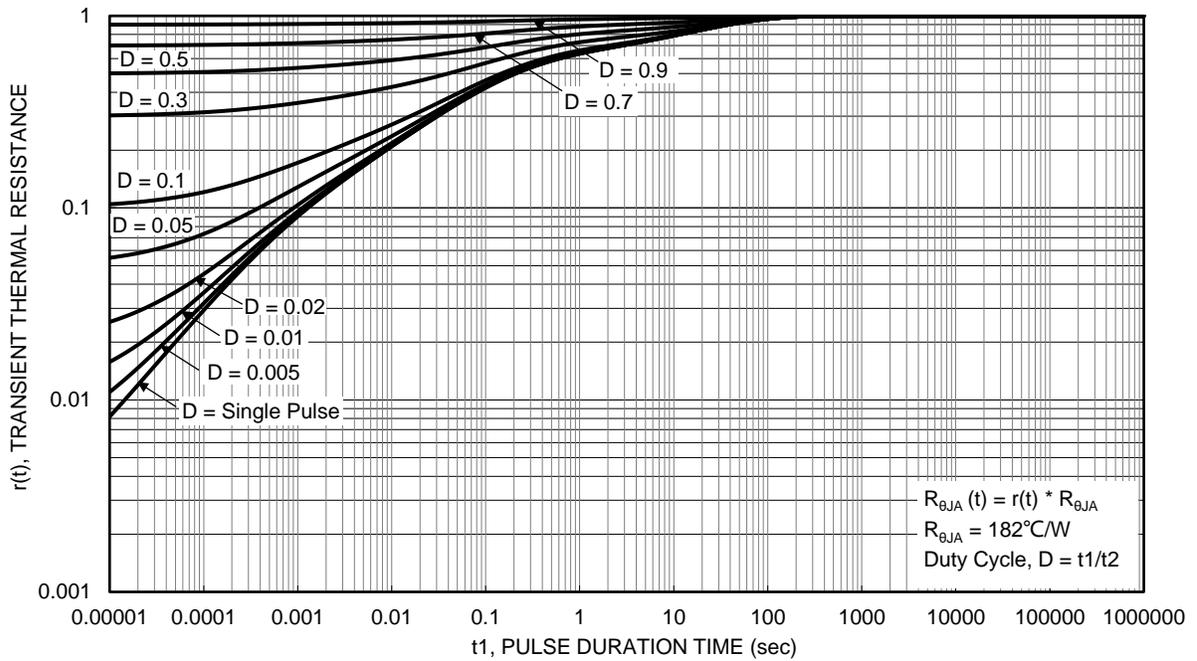
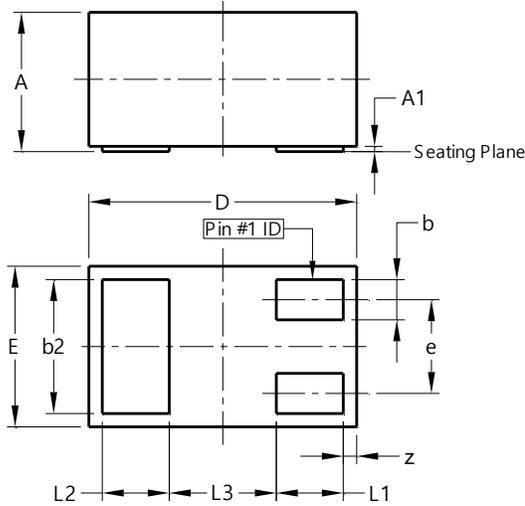


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3

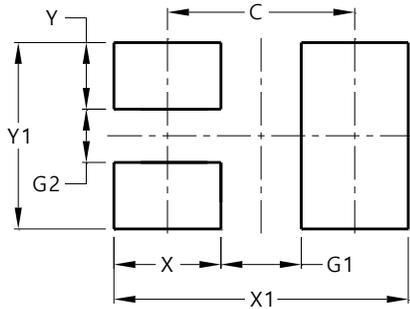


X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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